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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Active
Core Processor	PowerPC e300c3
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	333MHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	620-BBGA Exposed Pad
Supplier Device Package	620-HBGA (29x29)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8314cvrafda

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



This table shows the estimated typical I/O power dissipation for this family of devices.

Interface	Frequency	GV _{DD} (1.8 V)	GV _{DD} (2.5 V)	NV _{DD} (3.3 V)	LVDD1_OFF/ LVDD2_ON (3.3V)	LVDD2 _ON (3.3V)	VDD33PLL, VDD33ANA (3.3V)	SATA_VDD, VDD1IO, VDD1ANA (1.0V)	XCOREVDD, XPADVDD, SDAVDD (1.0V)	Unit
DDR 1 Rs = 22Ω	266MHz, 32 bits		0.323	—	—	_	_	_	—	W
$Rt = 50\Omega$	200MHz, 32 bits	_	0.291	—	—	_	_	_	—	W
DDR 2 Rs = 22Ω	266MHz, 32 bits	0.246	_	_	—	-	—	—	—	W
Rt = 75Ω	200MHz, 32bits	0.225	_	_	—	_	_	_	—	W
PCI I/O	33 MHz	-	—	0.120	—				—	W
load = 50pF	66 MHz		—	0.249	—			_	—	W
Local bus I/O	66 MHz	_	_		—	0.056	_	_	—	W
load = 20pF	50 MHz	_	_		—	0.040	_	_	—	W
eTSEC I/O	MII, 25MHz	_	—		0.008	_	_	_	—	W
Nultiple by number of	RGMII, 125MHz (3.3V)		_	_	0.078	_	_	_	_	V
used	RGMII, 125MHz (2.5V)	_	—	_	0.044	_	_	_	_	V
USBDR Controller (ULPI mode) Ioad =20pF	60 MHz	_	_	_	0.078	_	_	_		W
USBDR+ Internal PHY (UTMI mode)	480 MHz	_	_		0.274	_		_	—	W
PCI Express two x1lane	2.5 GHz	_	—	—	_	_	—	—	0.190	W
Other I/O	—	—		0.015	—	—	—	—	—	W

Table 5. MPC8314E Power Dissipation

5 Clock Input Timing

This section provides the clock input DC and AC electrical characteristics for the MPC8314E.



6 **RESET** Initialization

This section describes the DC and AC electrical specifications for the reset initialization timing and electrical requirements of the MPC8314E.

6.1 **RESET DC Electrical Characteristics**

This table provides the DC electrical characteristics for the RESET pins of the MPC8314E.

Characteristic	Symbol	Condition	Min	Мах	Unit
Input high voltage	V _{IH}	—	2.0	NVDD + 0.3	V
Input low voltage	V _{IL}	—	-0.3	0.8	V
Input current	I _{IN}	$0 \text{ V} \leq \text{ V}_{IN} \leq \text{ NVDD}$	_	±5	μΑ
Output high voltage	V _{OH}	I _{OH} = -8.0 mA	2.4	—	V
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	—	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	—	0.4	V

Table 8. RESET Pins DC Electrical Characteristics

6.2 **RESET AC Electrical Characteristics**

This table provides the reset initialization AC timing specifications of the MPC8314E.

Parameter/Condition	Min	Max	Unit	Note
Required assertion time of HRESET to activate reset flow	32		t _{PCI_SYNC_IN}	1
Required assertion time of PORESET with stable clock applied to SYS_CLK_IN when the device is in PCI host mode	32	—	t _{SYS_CLK_IN}	2
Required assertion time of PORESET with stable clock applied to PCI_SYNC_IN when the device is in PCI agent mode	32	—	^t PCI_SYNC_IN	1
HRESET assertion (output)	512		t _{PCI_SYNC_IN}	1
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:3] and CFG_SYS_CLKIN_DIV) with respect to negation of PORESET when the device is in PCI host mode	4	_	^t sys_clk_in	2, 4
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:3] and CFG_SYS_CLKIN_DIV) with respect to negation of PORESET when the device is in PCI agent mode	4	_	t _{PCI_SYNC_IN}	1
Input hold time for POR configuration signals with respect to negation of HRESET	0	—	ns	_
Time for the device to turn off POR configuration signals with respect to the assertion of HRESET	_	4	ns	3
Time for the device to turn on POR config signals with respect to the negation of HRESET	1	_	^t PCI_SYNC_IN	1, 3

Table 9. RESET Initialization Timing Specifications



DDR and DDR2 SDRAM

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions

Parameter	Symbol ¹	Min	Мах	Unit	Note
MCS[n] output hold with respect to MCK 266 MHz 200 MHz	t _{DDKHCX}	3.15 4.20		ns	3
MCK to MDQS Skew	t _{DDKHMH}	-0.6	0.6	ns	4
MDQ//MDM output setup with respect to MDQS 266 MHz 200 MHz	t _{DDKHDS,} t _{DDKLDS}	900 1000		ps	5
MDQ//MDM output hold with respect to MDQS 266 MHz 200 MHz	t _{DDKHDX,} t _{DDKLDX}	1100 1200	—	ps	5
MDQS preamble start	t _{DDKHMP}	$-0.5\times t_{MCK}-0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6
MDQS epilogue end	t _{DDKHME}	-0.6	0.6	ns	6

Note:

- The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state) (reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
 </sub>
- 2. All MCK/MCK referenced measurements are made from the crossing of the two signals ±0.1 V.
- 3. ADDR/CMD includes all DDR SDRAM output signals except MCK/MCK, MCS, and MDQ//MDM/MDQS.
- 4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the MPC8315E PowerQUICC II Pro Integrated Host Processor Family Reference Manual for a description and understanding of the timing modifications enabled by use of these bits.
- 5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
- 6. All outputs are referenced to the rising edge of MCK[n] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.



Ethernet: Three-Speed Ethernet, MII Management

Table 38. SGMII Receive AC Timing Specifications

At recommended operating conditions with XCOREVDD = $1.0V \pm 5\%$.

Parameter	Symbol	Min	Тур	Max	Unit	Note
Deterministic Jitter Tolerance	JD	0.37	—	_	UI p-p	1
Combined Deterministic and Random Jitter Tolerance	JDR	0.55	—	_	UI p-p	1
Sinusoidal Jitter Tolerance	JSIN	0.1	—	_	UI p-p	1
Total Jitter Tolerance	JT	0.65	—	_	UI p-p	1
Bit Error Ratio	BER	—	—	10 ⁻¹²		
Unit Interval	UI	799.92	800	800.08	ps	2
AC Coupling Capacitor	C _{TX}	5	—	200	nF	3

Note:

1. Measured at receiver.

2. Each UI is 800 ps ± 100 ppm.

The external AC coupling capacitor is required. It's recommended to be placed near the device transmitter outputs.
 Refer to RapidIOTM 1x/4x LP Serial Physical Layer Specification for interpretation of jitter specifications.



Figure 19. SGMII Receiver Input Compliance Mask







Figure 25. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2





12.2 JTAG AC Timing Specifications

This section describes the AC electrical specifications for the IEEE 1149.1 (JTAG) interface. This table provides the JTAG AC timing specifications as defined in Figure 28 through Figure 31.

Table 46. JTAG AC Timing Specifications (Independent of SYS_CLK_IN)¹

At recommended operating conditions (see Table 2)

Parameter	Symbol ²	Min	Max	Unit	Note
JTAG external clock frequency of operation	f _{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t _{JTG}	30	—	ns	—
JTAG external clock pulse width measured at 1.4 V	t _{JTKHKL}	15	—	ns	—
JTAG external clock rise and fall times	t _{JTGR} , t _{JTGF}	0	2	ns	—
TRST assert time	t _{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	t _{JTDVKH} t _{JTIVKH}	4 4	_	ns	4
Input hold times: Boundary-scan data TMS, TDI	t _{JTDXKH} t _{JTIXKH}	10 10	_	ns	4
Valid times: Boundary-scan data TDO	t _{JTKLDV} t _{JTKLOV}	2 2	11 11	ns	5
Output hold times: Boundary-scan data TDO	t _{jtkldx} t _{jtklox}	2 2	_	ns	5
JTAG external clock to output high impedance: Boundary-scan data TDO	t _{jtkldz} t _{jtkloz}	2 2	19 9	ns	5, 6

Note:

 All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Table 27). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.

- 2. The symbols used for timing specifications herein follow the pattern of t_{(first two letters of functional block)(signal)(state)} (reference)(state) for inputs and t_(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
- 3. TRST is an asynchronous level sensitive signal. The setup time is for test purposes only.
- 4. Non-JTAG signal input timing with respect to t_{TCLK}.
- 5. Non-JTAG signal output timing with respect to t_{TCLK}.
- 6. Guaranteed by design and characterization.



High-Speed Serial Interfaces (HSSI)



Differential Peak-Peak Voltage, VDIFFpp = 2*VDIFFp (not shown)

Figure 37. Differential Voltage Definitions for Transmitter or Receiver

To illustrate these definitions using real values, consider the case of a CML (Current Mode Logic) transmitter that has a common mode voltage of 2.25 V and each of its outputs, TD and TD, has a swing that goes between 2.5V and 2.0V. Using these values, the peak-to-peak voltage swing of each signal (TD or TD) is 500 mV p-p, which is referred as the single-ended swing for each signal. In this example, since the differential signaling environment is fully symmetrical, the transmitter output's differential swing (V_{OD}) has the same amplitude as each signal's single-ended swing. The differential output signal ranges between 500 mV and -500 mV, in other words, V_{OD} is 500 mV in one phase and -500 mV in the other phase. The peak differential voltage (V_{DIFFp}) is 500 mV. The peak-to-peak differential voltage (V_{DIFFp}) is 1000 mV p-p.

15.2 SerDes Reference Clocks

The SerDes reference clock inputs are applied to an internal PLL whose output creates the clock used by the corresponding SerDes lanes. The SerDes reference clocks input is SD_REF_CLK and SD_REF_CLK for PCI Express and SGMII interface.

The following sections describe the SerDes reference clock requirements and some application information.

15.2.1 SerDes Reference Clock Receiver Characteristics

Figure 38 shows a receiver reference diagram of the SerDes reference clocks.

- The supply voltage requirements for XCOREVDD are specified in Table 1 and Table 2.
- SerDes Reference Clock Receiver Reference Circuit Structure
 - The SD_REF_CLK and SD_REF_CLK are internally AC-coupled differential inputs as shown in Figure 38. Each differential clock input (SD_REF_CLK or SD_REF_CLK) has a 50-Ω termination to XCOREVSS followed by on-chip AC-coupling.
 - The external reference clock driver must be able to drive this termination.
 - The SerDes reference clock input can be either differential or single-ended. Refer to the Differential Mode and Single-ended Mode description below for further detailed requirements.



16 PCI Express

This section describes the DC and AC electrical specifications for the PCI Express bus of the MPC8315E.

16.1 DC Requirements for PCI Express SD_REF_CLK and SD_REF_CLK

For more information, see Section 15.2, "SerDes Reference Clocks."

16.2 AC Requirements for PCI Express SerDes Clocks

This table lists the PCI Express SerDes clock AC requirements.

Table 53. SD_I	REF_CLK and	SD_REF_CLK	AC Requirements
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Symbol	Parameter Description	Min	Тур	Max	Unit	Note
t _{REF}	REFCLK cycle time	_	10	—	ns	—
t _{REFCJ}	REFCLK cycle-to-cycle jitter. Difference in the period of any two adjacent REFCLK cycles.	—		100	ps	—
t _{REFPJ}	Phase jitter. Deviation in edge location with respect to mean edge location.	-50	_	50	ps	—

16.3 Clocking Dependencies

The ports on the two ends of a link must transmit data at a rate that is within 600 parts per million (ppm) of each other at all times. This is specified to allow bit rate clock sources with a ± 300 ppm tolerance.

16.4 Physical Layer Specifications

Following is a summary of the specifications for the physical layer of PCI Express on this device. For further details as well as the specifications of the transport and data link layer please use the *PCI Express Base Specification*, Rev. 1.0a.

16.4.1 Differential Transmitter (TX) Output

This table defines the specifications for the differential output at all transmitters (TXs). The parameters are specified at the component pins.

Parameter	Symbol	Comments	Min	Typical	Max	Unit	Note
Unit interval	UI	Each UI is 400 ps \pm 300 ppm. UI does not account for Spread Spectrum Clock dictated variations.	399.88	400	400.12	ps	1
Differential peak-to-peak output voltage	V _{TX-DIFFp-p}	$V_{TX-DIFFp-p} = 2^* V_{TX-D+} - V_{TX-D-} $	0.8	_	1.2	V	2

Table 54. Differential Transmitter (TX) Output Specifications



PCI Express

Parameter	Symbol	Comments	Min	Typical	Max	Unit	Note
De-Emphasized differential output voltage (ratio)	V _{TX-DE-RATIO}	Ratio of the $V_{TX-DIFFp-p}$ of the second and following bits after a transition divided by the $V_{TX-DIFFp-p}$ of the first bit after a transition.	-3.0	-3.5	-4.0	dB	2
Minimum TX eye width	T _{TX-EYE}	The maximum Transmitter jitter can be derived as $T_{TX-MAX-JITTER} = 1 - U_{TX-EYE} = 0.3$ UI.	0.70	_	—	UI	2, 3
Maximum time between the jitter median and maximum deviation from the median	T _{TX-EYE-MEDIAN-to-} MAX-JITTER	Jitter is defined as the measurement variation of the crossing points $(V_{TX-DIFFp-p} = 0 V)$ in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.	_	_	0.15	UI	2, 3
D+/D- TX output rise/fall time	$T_{TX-RISE}$, $T_{TX-FALL}$	—	0.125		_	UI	2, 5
RMS AC peak common mode output voltage	V _{TX-CM-ACp}	$\begin{split} & V_{TX-CM-ACp} = RMS(V_{TXD+} + V_{TXD-} /2 - V_{TX-CM-DC}) \\ & V_{TX-CM-DC} = DC_{(avg)} \text{ of } V_{TX-D+} + V_{TX-D-} /2 \end{split}$	_	_	20	mV	2
Absolute delta of DC common mode voltage during L0 and electrical idle	V _{TX-CM-DC-} ACTIVE- IDLE-DELTA	$\label{eq:loss} \begin{array}{l} V_{TX-CM-DC} \ (during \ L0) \ \ V_{TX-CM-Idle-DC} \\ (During \ Electrical \ Idle) <= 100 \ \ mV \\ V_{TX-CM-DC} \ = \ DC_{(avg)} \ of \ V_{TX-D+} \ + \ V_{TX-D-} /2 \\ [L0] \\ V_{TX-CM-Idle-DC} \ = \ DC_{(avg)} \ of \ V_{TX-D+} \ + \\ V_{TX-D-} /2 \ \ [Electrical \ Idle] \end{array}$	0		100	mV	2
Absolute delta of DC common mode between D+ and D–	VTX-CM-DC-LINE-DELTA	$\begin{split} V_{\text{TX-CM-DC-D+}} - V_{\text{TX-CM-DC-D-}} &<= 25 \text{ mV} \\ V_{\text{TX-CM-DC-D+}} = DC_{(\text{avg})} \text{ of } V_{\text{TX-D+}} \\ V_{\text{TX-CM-DC-D-}} = DC_{(\text{avg})} \text{ of } V_{\text{TX-D-}} \end{split}$	0	_	25	mV	2
Electrical idle differential peak output voltage	V _{TX-IDLE} -DIFFp	$V_{TX-IDLE-DIFFp} = V_{TX-IDLE-D+} - V_{TX-IDLE-D-} $ <= 20 mV	0	—	20	mV	2
Amount of voltage change allowed during receiver detection	V _{TX-RCV-DETECT}	The total amount of voltage change that a transmitter can apply to sense whether a low impedance Receiver is present.	_	_	600	mV	6
TX DC common mode voltage	V _{TX-DC-CM}	The allowed DC Common Mode voltage under any conditions.	_	—	3.6	V	6
TX short circuit current limit	I _{TX-SHORT}	The total current the Transmitter can provide when shorted to its ground	_	_	90	mA	—
Minimum time spent in electrical idle	T _{TX-IDLE-MIN}	Minimum time a Transmitter must be in Electrical Idle Utilized by the Receiver to start looking for an Electrical Idle Exit after successfully receiving an Electrical Idle ordered set	50	_		UI	



PCI Express

16.4.2 Transmitter Compliance Eye Diagrams

The TX eye diagram in Figure 49 is specified using the passive compliance/test measurement load (see Figure 51) in place of any real PCI Express interconnect + RX component. There are two eye diagrams that must be met for the transmitter. Both diagrams must be aligned in time using the jitter median to locate the center of the eye diagram. The different eye diagrams differ in voltage depending on whether it is a transition bit or a de-emphasized bit. The exact reduced voltage level of the de-emphasized bit is always relative to the transition bit.

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

It is recommended that the recovered TX UI be calculated using all edges in the 3500 consecutive UI interval with a fit algorithm using a minimization merit function (that is, least squares and median deviation fits).



Figure 49. Minimum Transmitter Timing and Voltage Output Compliance Specifications



16.5 Receiver Compliance Eye Diagrams

The RX eye diagram in Figure 50 is specified using the passive compliance/test measurement load (see Figure 51) in place of any real PCI Express RX component. In general, the minimum receiver eye diagram measured with the compliance/test measurement load (see Figure 51) is larger than the minimum receiver eye diagram measured over a range of systems at the input receiver of any real PCI Express component. The degraded eye diagram at the input Receiver is due to traces internal to the package as well as silicon parasitic characteristics which cause the real PCI Express component to vary in impedance from the compliance/test measurement load. The input receiver eye diagram is implementation specific and is not specified. RX component designer should provide additional margin to adequately compensate for the degraded minimum Receiver eye diagram (shown in Figure 50) expected at the input receiver based on an adequate combination of system simulations and the return loss measured looking into the RX package and silicon. The RX eye diagram must be aligned in time using the jitter median to locate the center of the eye diagram.

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

The reference impedance for return loss measurements is 50 Ω to ground for both the D+ and D- line (that is, as measured by a Vector Network Analyzer with 50 Ω probes—see Figure 51). Note that the series capacitors, C_{PEACCTX}, are optional for the return loss measurement.





16.5.1 Compliance Test and Measurement Load

The AC timing and voltage parameters must be verified at the measurement point, as specified within 0.2 inches of the package pins, into a test/measurement load shown in Figure 51.



NOTE

The allowance of the measurement point to be within 0.2 inches of the package pins is meant to acknowledge that package/board routing may benefit from D+ and D- not being exactly matched in length at the package pin boundary.



Figure 51. Compliance Test/Measurement Load

17 Timers

This section describes the DC and AC electrical specifications for the timers of the MPC8314E.

17.1 Timers DC Electrical Characteristics

This table provides the DC electrical characteristics for the timers pins, including TIN, $\overline{\text{TOUT}}$, $\overline{\text{TGATE}}$, and RTC_CLK.

Characteristic	Symbol	Condition	Min	Мах	Unit
Output high voltage	V _{OH}	I _{OH} = -8.0 mA	2.4	—	V
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	_	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	_	0.4	V
Input high voltage	V _{IH}	_	2.1	NVDD + 0.3	V
Input low voltage	V _{IL}	_	-0.3	0.8	V
Input current	I _{IN}	$0~V \leq V_{IN} \leq NVDD$	_	± 5	μA

Table 56. Timers DC Electrical Characteristics

17.2 Timers AC Timing Specifications

This table provides the timers input and output AC timing specifications.

Table 57. Timers Input AC Timing Specifications

Characteristic	Symbol ¹	Min	Unit
Timers inputs—minimum pulse width	t _{TIWID}	20	ns



This figure shows the TDM transmit signal timing.



5

22 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8314E is available in a thermally enhanced plastic ball grid array (TEPBGA II), see Section 22.1, "Package Parameters for the MPC8314E TEPBGA II," and Section 22.2, "Mechanical Dimensions of the TEPBGA II," for information on the TEPBGA II.

22.1 Package Parameters for the MPC8314E TEPBGA II

The package parameters are as provided in the following list. The package type is 29 mm \times 29 mm, TEPBGA II.

$29 \text{ mm} \times 29 \text{ mm}$
620
1 mm
2.23 mm
96.5 Sn/3.5 Ag (VR package)
0.6 mm



Table 66. MPC8314E TEPBGA II Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Note		
	DDR Memory Controller Interface					
MEMC_MDQ[0]	AF16	I/O	GVDD	_		
MEMC_MDQ[1]	AE17	I/O	GVDD	—		
MEMC_MDQ[2]	AH17	I/O	GVDD	—		
MEMC_MDQ[3]	AG17	I/O	GVDD	—		
MEMC_MDQ[4]	AG18	I/O	GVDD	—		
MEMC_MDQ[5]	AH18	I/O	GVDD	—		
MEMC_MDQ[6]	AD18	I/O	GVDD	_		
MEMC_MDQ[7]	AF19	I/O	GVDD	_		
MEMC_MDQ[8]	AH19	I/O	GVDD	—		
MEMC_MDQ[9]	AD19	I/O	GVDD	_		
MEMC_MDQ[10]	AG20	I/O	GVDD	—		
MEMC_MDQ[11]	AH20	I/O	GVDD	—		
MEMC_MDQ[12]	AH21	I/O	GVDD	_		
MEMC_MDQ[13]	AE21	I/O	GVDD	—		
MEMC_MDQ[14]	AH22	I/O	GVDD	—		
MEMC_MDQ[15]	AD21	I/O	GVDD	_		
MEMC_MDQ[16]	AG10	I/O	GVDD	-		
MEMC_MDQ[17]	AH9	I/O	GVDD	-		
MEMC_MDQ[18]	AH8	I/O	GVDD	_		
MEMC_MDQ[19]	AD11	I/O	GVDD			
MEMC_MDQ[20]	AH7	I/O	GVDD	-		
MEMC_MDQ[21]	AG7	I/O	GVDD	_		
MEMC_MDQ[22]	AF8	I/O	GVDD	_		
MEMC_MDQ[23]	AD10	I/O	GVDD	_		
MEMC_MDQ[24]	AE9	I/O	GVDD	_		
MEMC_MDQ[25]	AH6	I/O	GVDD	—		
MEMC_MDQ[26]	AH5	I/O	GVDD	—		
MEMC_MDQ[27]	AG6	I/O	GVDD	_		
MEMC_MDQ[28]	AH4	I/O	GVDD	—		
MEMC_MDQ[29]	AE6	I/O	GVDD			
MEMC_MDQ[30]	AD8	I/O	GVDD	—		
MEMC_MDQ[31]	AF5	I/O	GVDD	—		
MEMC_MDM0	AE18	0	GVDD			
MEMC_MDM1	AE20	0	GVDD	—		
MEMC_MDM2	AE10	0	GVDD	—		



Table 66	. MPC8314E	TEPBGA II	Pinout L	isting (continued)
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Signal	Package Pin Number	Pin Type	Power Supply	Note
	Local Bus Controller Interface			
LAD0	AB28	I/O	NVDD3_OFF	10
LAD1	AB27	I/O	NVDD3_OFF	10
LAD2	AC28	I/O	NVDD3_OFF	10
LAD3	AA24	I/O	NVDD3_OFF	10
LAD4	AC27	I/O	NVDD3_OFF	10
LAD5	AD28	I/O	NVDD3_OFF	10
LAD6	AB25	I/O	NVDD3_OFF	10
LAD7	AC26	I/O	NVDD3_OFF	10
LAD8	AD27	I/O	NVDD3_OFF	10
LAD9	AB24	I/O	NVDD3_OFF	10
LAD10	AE28	I/O	NVDD3_OFF	10
LAD11	AE27	I/O	NVDD3_OFF	10
LAD12	AE26	I/O	NVDD3_OFF	10
LAD13	AF28	I/O	NVDD3_OFF	10
LAD14	AC24	I/O	NVDD3_OFF	10
LAD15	AD25	I/O	NVDD3_OFF	10
LA16	V24	0	NVDD3_OFF	10
LA17	V25	0	NVDD3_OFF	10
LA18	W26	0	NVDD3_OFF	10
LA19	W28	0	NVDD3_OFF	10
LA20	U24	0	NVDD3_OFF	10
LA21	W24	0	NVDD3_OFF	10
LA22	Y28	0	NVDD3_OFF	10
LA23	AH23	0	NVDD3_OFF	10
LA24	AH24	0	NVDD3_OFF	10
LA25	AG23	0	NVDD3_OFF	10
LCS[0]	AD22	0	NVDD3_OFF	11
LCS[1]	AF25	0	NVDD3_OFF	11
LCS[2]	AG24	0	NVDD3_OFF	11
LCS[3]	AF24	0	NVDD3_OFF	11
LWE[0] /LFWE/LBS	AE23	0	NVDD3_OFF	11
LWE[1]	AG26	0	NVDD3_OFF	11
LBCTL	AH26	0	NVDD3_OFF	11
LALE	AF26	0	NVDD3_OFF	10
LGPL0/LFCLE	Y27	0	NVDD3_OFF	—



Signal	Package Pin Number	Pin Type	Power Supply	Note
PCI_AD[23]	C22	I/O	NVDD2_OFF	-
PCI_AD[24]	E19	I/O	NVDD2_OFF	—
PCI_AD[25]	A22	I/O	NVDD2_OFF	—
PCI_AD[26]	C20	I/O	NVDD2_OFF	—
PCI_AD[27]	B21	I/O	NVDD2_OFF	-
PCI_AD[28]	D19	I/O	NVDD2_OFF	—
PCI_AD[29]	A19	I/O	NVDD2_OFF	—
PCI_AD[30]	A21	I/O	NVDD2_OFF	—
PCI_AD[31]	B19	I/O	NVDD2_OFF	—
PCI_C/BE[0]	H24	I/O	NVDD2_OFF	—
PCI_C/BE[1]	C27	I/O	NVDD2_OFF	—
PCI_C/BE[2]	A25	I/O	NVDD2_OFF	—
PCI_C/BE[3]	E21	I/O	NVDD2_OFF	—
PCI_PAR	G24	I/O	NVDD2_OFF	-
PCI_FRAME	C28	I/O	NVDD2_OFF	5
PCI_TRDY	A24	I/O	NVDD2_OFF	5
PCI_IRDY	D25	I/O	NVDD2_OFF	5
PCI_STOP	D23	I/O	NVDD2_OFF	5
PCI_DEVSEL	E22	I/O	NVDD2_OFF	5
PCI_IDSEL	D26	I	NVDD2_OFF	—
PCI_SERR	C25	I/O	NVDD2_OFF	5
PCI_PERR	D21	I/O	NVDD2_OFF	5
PCI_REQ0	E18	I/O	NVDD2_OFF	—
PCI_REQ1/CPCI_HS_ES	C18	I	NVDD2_OFF	—
PCI_REQ2	E17	I	NVDD2_OFF	—
PCI_GNT0	B20	I/O	NVDD2_OFF	—
PCI_GNT1/CPCI_HS_LED	D17	0	NVDD2_OFF	—
PCI_GNT2/CPCI_HS_ENUM	E15	0	NVDD2_OFF	—
M66EN	L24	I	NVDD2_OFF	—
PCI_CLK0	E23	0	NVDD2_OFF	—
PCI_CLK1	F24	0	NVDD2_OFF	—
PCI_CLK2	E25	0	NVDD2_OFF	—
PCI_PME	B23	I/O	NVDD2_OFF	2
	ETSEC1/_USBULPI			<u> </u>
GPIO_24/TSEC1_COL/USBDR_TXDRXD0	J1	I/O	LVDD1_OFF	_
GPIO_25/TSEC1_CRS/USBDR_TXDRXD1	H1	I/O	LVDD1 OFF	_

Table 66. MPC8314E TEPBGA II Pinout Listing (continued)



Clocking

Table 67. Configurable Clock Units

Unit	Default Frequency	Options
eTSEC1	csb_clk	Off, csb_clk, csb_clk/2, csb_clk/3
eTSEC2	csb_clk	Off, csb_clk, csb_clk/2, csb_clk/3
Security Core, I2C, SAP, TPR	csb_clk	Off, csb_clk, csb_clk/2, csb_clk/3
USB DR	csb_clk	Off, csb_clk, csb_clk/2, csb_clk/3
PCI and DMA complex	csb_clk	Off, csb_clk
PCI Express	csb_clk	Off, csb_clk
Serial ATA	csb_clk	Off, csb_clk, csb_clk/2, csb_clk/3

This table provides the operating frequencies for the TEPBGA II under recommended operating conditions (see Table 2).

Table 68. C	perating	Frequencies	for TEPBGA II
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Characteristic ¹	Max Operating Frequency	Unit
e300 core frequency (<i>core_clk</i>)	400	MHz
Coherent system bus frequency (csb_clk)	133	MHz
DDR1/2 memory bus frequency (MCK) ²	133	MHz
Local bus frequency (LCLKn) ³	66	MHz
PCI input frequency (SYS_CLK_IN or PCI_CLK)	24-66	MHz

Note:

1. The SYS_CLK_IN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen such that the resulting *csb_clk*, MCK, LCLK[0:1], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies.

2. The DDR data rate is 2x the DDR memory bus frequency.

3. The local bus frequency is 1/2, 1/4, or 1/8 of the *lbiu_clk* frequency (depending on LCRR[CLKDIV]) which is in turn 1x or 2x the *csb_clk* frequency (depending on RCWL[LBCM]).

23.1 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] parameter. Table 69 shows the multiplication factor encodings for the system PLL.

NOTE

If RCWL[DDRCM] and RCWL[LBCM] are both cleared, the system PLL VCO frequency = (CSB frequency) × (System PLL VCO Divider).

If either RCWL[DDRCM] or RCWL[LBCM] are set, the system PLL VCO frequency = $2 \times (CSB \text{ frequency}) \times (System PLL VCO Divider).$

The VCO divider needs to be set properly so that the System PLL VCO frequency is in the range of 450–750 MHz.



Thermal

24.2.3 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, the Thermal Characterization Parameter (Ψ_{JT}) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using the following equation:

 $T_J = T_T + (\Psi_{JT} \times P_D)$ where: $T_J = \text{junction temperature (°C)}$ $T_T = \text{thermocouple temperature on top of package (°C)}$ $\Psi_{JT} = \text{junction to ambient thermal resistance (°C/W)}$ $P_D = \text{power dissipation in the package (W)}$

The thermal characterization parameter is measured per JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

24.2.4 Heat Sinks and Junction-to-Case Thermal Resistance

In some application environments, a heat sink is required to provide the necessary thermal management of the device. When a heat sink is used, the thermal resistance is expressed as the sum of a junction to case thermal resistance and a case to ambient thermal resistance:

 $R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$ where: $R_{\theta JA} = \text{junction to ambient thermal resistance (°C/W)}$ $R_{\theta JC} = \text{junction to case thermal resistance (°C/W)}$ $R_{\theta CA} = \text{case to ambient thermal resistance (°C/W)}$

 $R_{\theta JC}$ is device related and cannot be influenced by the user. The user controls the thermal environment to change the case to ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed circuit board, or change the thermal dissipation on the printed circuit board surrounding the device.

To illustrate the thermal performance of the devices with heat sinks, the thermal performance has been simulated with a few commercially available heat sinks. The heat sink choice is determined by the application environment (temperature, air flow, adjacent component power dissipation) and the physical space available. Because there is not a standard application environment, a standard heat sink is not required.



System Design Information

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum Effective Series Inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

Each circuit should be placed as close as possible to the specific AV_{DD} pin being supplied to minimize noise coupled from nearby circuits. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of package, without the inductance of vias. Note that the RC filter results in lower voltage level on AVDD. This does not imply that the DC specification can be relaxed.

This figure shows the PLL power supply filter circuit.



Figure 61. PLL Power Supply Filter Circuit

25.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the device can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8314E system, and the MPC8314E itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each VDD, NVDD, GVDD, and LVDD pins of the device. These decoupling capacitors should receive their power from separate VDD, NVDD, GVDD, GVDD, and GND power planes in the PCB, utilizing thick and short traces to minimize inductance. Capacitors may be placed directly under the device using a standard escape pattern. Others may surround the part.

These capacitors should have a value of 0.01 or 0.1 μ F. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the VDD, NVDD, GVDD, and LVDD planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors— $100-330 \mu F$ (AVX TPS tantalum or Sanyo OSCON).

25.4 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. Unused active low inputs should be tied to NVDD, GVDD, or LVDD as required. Unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected.



Revision History

27 Revision History

This table summarizes a revision history for this document.

Table	79.	Revision	History

Revision	Date	Substantive Change(s)
2	11/2011	 In Table 66: Corrected Note 10 to pull down. Added pull up information.
1	11/2011	 Added Notes 4, 5, 6, and 7 in Table 2. In Table 6: Decoupled PCI_CLK and SYS_CLK_IN rise and fall times. Relaxed maximum rise/fall time of SYS_CLK_IN from 1.2 ns to 4 ns. Modified Note 2. Updated SYS_CLK_IN/PCI_CLK frequency from 66 MHz to 66.67 MHz. Added note 4 to Table 9. Added a note stating "eTSEC should be interfaced with peripheral operating at same voltage level." in Section 9.1.1, "MII, RGMII, and RTBI DC Electrical Characteristics." Added a note in Table 26 stating "The frequency of RX_CLK should not exceed the TX_CLK by more than 300 ppm." Added a note in Table 29 stating "The frequency of RX_CLK should not exceed the GTX_CLK125 by more than 300 ppm." Added t₁ALEHOV parameter to Table 44 Replaced 50 with 50 Ω in Section 16.5, "Receiver Compliance Eye Diagrams." In Table 66: Added Pull up and Pull down information. Removed Note 2 from TSEC_MDIO. Removed Configuration 2 from Table 73. Removed MDIO signal from Section 25.7, "Pull-Up Resistor Requirements" as this signal is not open drain. Replaced SYS_CLK Nwith SYS_CLK_IN throughout. Replaced all LBIUCM with LBCM. Replaced all SYS_CR_CLK_IN and SYS_CR_CLK_OUT with SYS_XTAL_IN and SYS_XTAL_OUT, respectively. Replaced all USB_CR_CLK_IN and USB_CR_CLK_OUT with USB_XTAL_OUT, with CLK
0	05/2009	Initial public release